

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI TVU 025 is Designed for

FEATURES:

- Input Matching Network
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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CB0}	45 V
V_{CEO}	30 V
V_{EBO}	3.0 V
P_{DISS}	135 W @ T _C = 25 °C
T_J	-50 °C to +200 °C
T_{STG}	-50 °C to +150 °C
θ_{JC}	1.3 °C/W

PACKAGE STYLE .450 BAL FLG(A)

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.055 / 1.40	
B	.120 / 3.05	.130 / 3.30
C	.785 / 19.94	
D	.455 / 11.56	.465 / 11.81
E	.120 / 3.05	.130 / 3.30
F	.230 / 5.84	
G	.838 / 21.28	.850 / 21.59
H	1.095 / 27.81	1.105 / 28.07
J	.525 / 13.34	.535 / 13.59
K	.002 / 0.05	.005 / 0.15
L	.055 / 1.40	.065 / 1.65
M	.080 / 2.03	.095 / 2.41
N	.195 / 4.95	
P	.445 / 11.30	.455 / 11.56

ORDER CODE: ASI10650

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 50 mA	45			V
BV_{CEO}	I _C = 200 mA	30			V
BV_{EBO}	I _E = 10 mA	3.0			V
I_{CEO}	V _{CE} = 25 V			5.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 3.0 A	10		80	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz		70		pF
P_G IMD₁	V _{CE} = 25 V I _C = 3.2 A f = 860 MHz P _{OUT} = 25 W	8.0 -45			dB dBc